OptiMOS®-T2 Power-Transistor

AEC Qualified

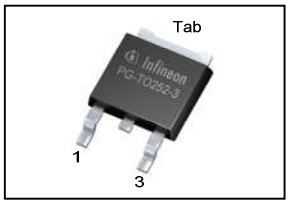
RoHS

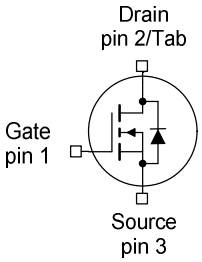
Product Summary

V_{DS}	30	V
$R_{DS(on),max}$	5.5	mΩ
I_D	50	A

- N-channel - Enhancement mode
- Automotive AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested

PG-TO252-3-11





Type	Package	Marking
IPD50N03S4L-06	PG-TO252-3-11	4N03L06

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current[1]	I_D	T_C=25°C, V_{GS}=10V	50	A
		T_C=100°C, V_{GS}=10V[2]	50	
Pulsed drain current[2]	$I_{D,pulse}$	T_C=25°C	200	
Avalanche energy, single pulse[2]	E_{AS}	I_D=50A	36	mJ
Avalanche current, single pulse	I_{AS}	-	50	A
Gate source voltage	V_{GS}	-	±16	V
Power dissipation	P_{tot}	T_C=25°C	56	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	–

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	-	2.7	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm^2 cooling area[3)]	-	-	40	

Electrical characteristics, at T_j=25 °C, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D= 1mA	30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=20µA	1.0	1.5	2.2	
Zero gate voltage drain current	I_{DSS}	V_{DS}=30V, V_{GS}=0V, T_j=25°C	-	0.1	1	µA
		V_{DS}=30V, V_{GS}=0V, T_j=125°C[2)]	-	10	100	
Gate-source leakage current	I_{GSS}	V_{GS}=16V, V_{DS}=0V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=4.5V, I_D=25A	-	6.9	9.0	mΩ
		V_{GS}= 10V, I_D=50 A	-	4.9	5.5	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz	-	1790	2330	pF
Output capacitance	C_{oss}		-	460	600	
Reverse transfer capacitance	C_{rss}		-	17	34	
Turn-on delay time	$t_{d(on)}$	V_{DD}=15V, V_{GS}=10V, I_D=30A, R_G=1.6Ω	-	3	-	ns
Rise time	t_r		-	1	-	
Turn-off delay time	$t_{d(off)}$		-	19	-	
Fall time	t_f		-	7	-	
Gate Charge Characteristics[2)]						
Gate to source charge	Q_{gs}	V_{DD}=24V, I_D=50A, V_{GS}=0 to 10V	-	6	8	nC
Gate to drain charge	Q_{gd}		-	3	6	
Gate charge total	Q_g		-	24	31	
Gate plateau voltage	$V_{plateau}$		-	3.2	-	V
Reverse Diode						
Diode continous forward current[2)]	I_S	T_C=25°C	-	-	50	A
Diode pulse current[2)]	$I_{S,pulse}$		-	-	200	
Diode forward voltage	V_{SD}	V_{GS}=0V, I_F=50A, T_j=25°C	0.6	0.95	1.3	V
Reverse recovery time[2)]	t_{rr}	V_R=30V, I_F=I_S, di_F/dt=100A/µs	-	17	-	ns
Reverse recovery charge[2)]	Q_{rr}		-	14	-	nC

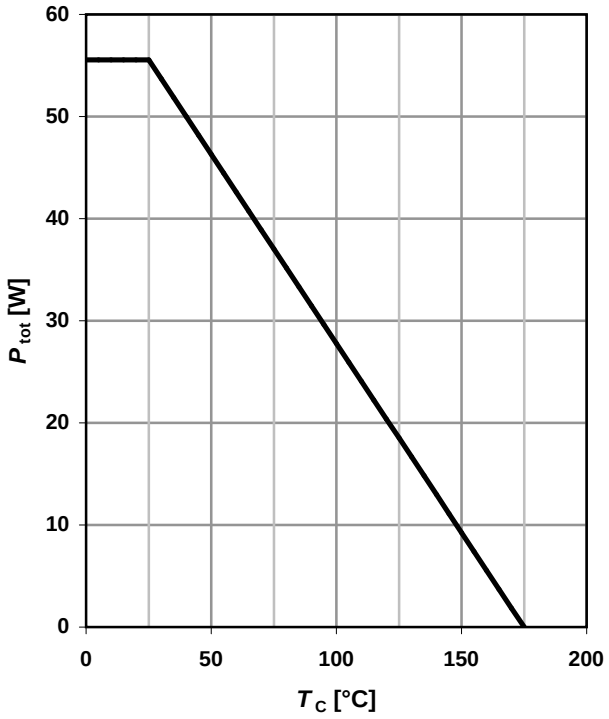
[1)] Current is limited by bondwire; with an R_{thJC} = 2.7K/W the chip is able to carry 77A at 25°C.

[2)] Defined by design. Not subject to production test.

[3)] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

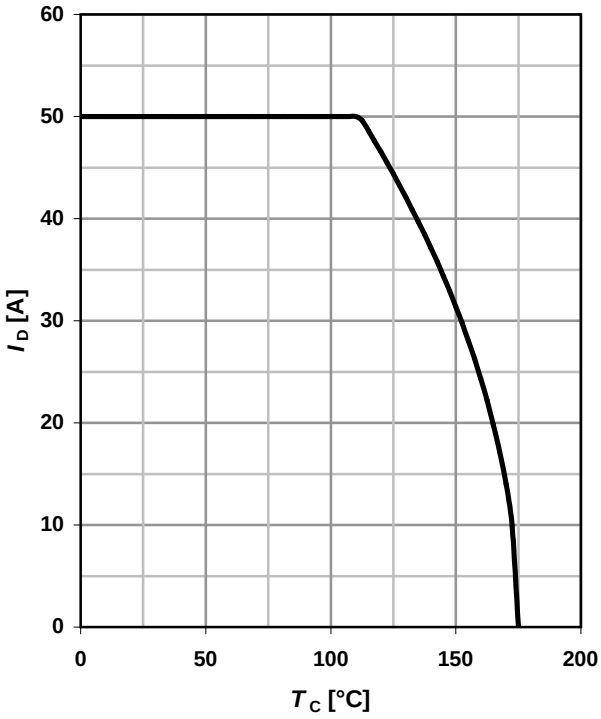
1 Power dissipation

$P_{tot} = f(T_C)$; $V_{GS} \geq 6$ V



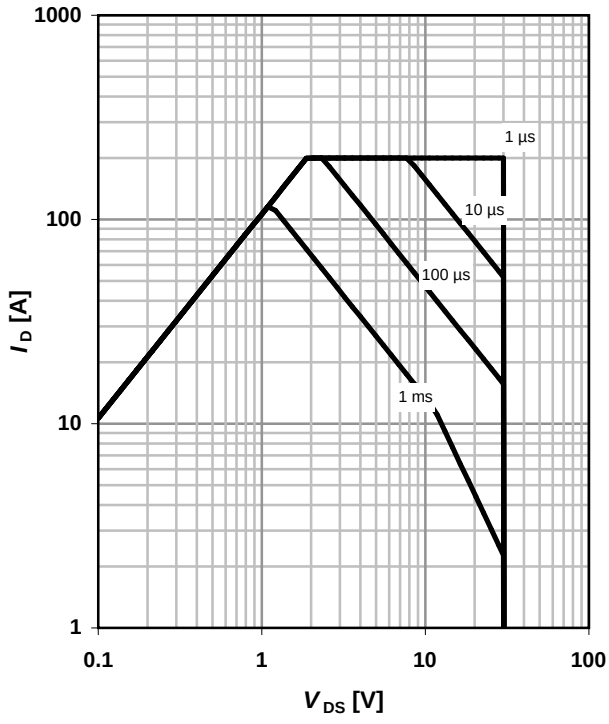
2 Drain current

$I_D = f(T_C)$; $V_{GS} \geq 6$ V



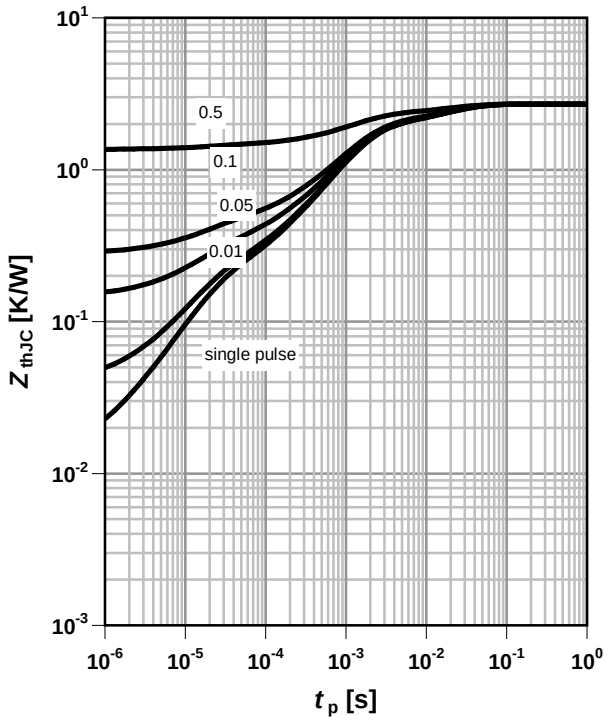
$I_D = f(V_{DS})$; $T_C = 25$ °C; $D = 0$

parameter: t_p



$Z_{thJC} = f(t_p)$

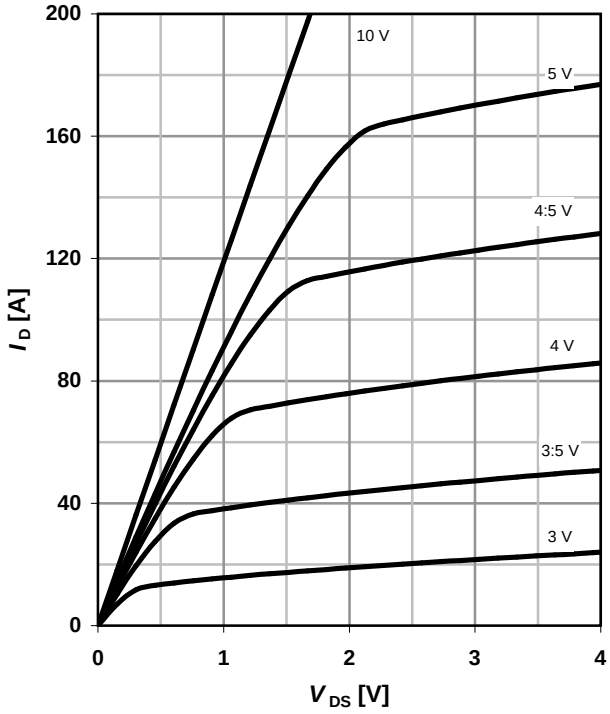
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS})$; $T_j = 25$ °C

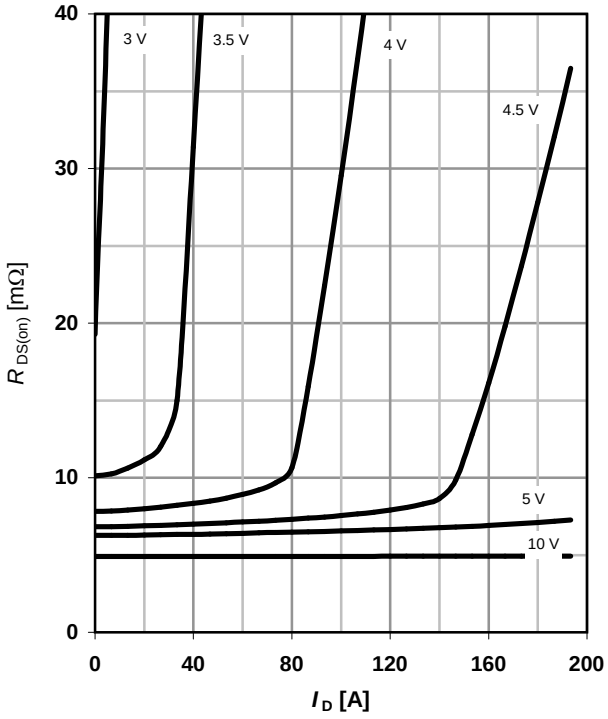
parameter: V_{GS}



6 Typ. drain-source on-state resistance

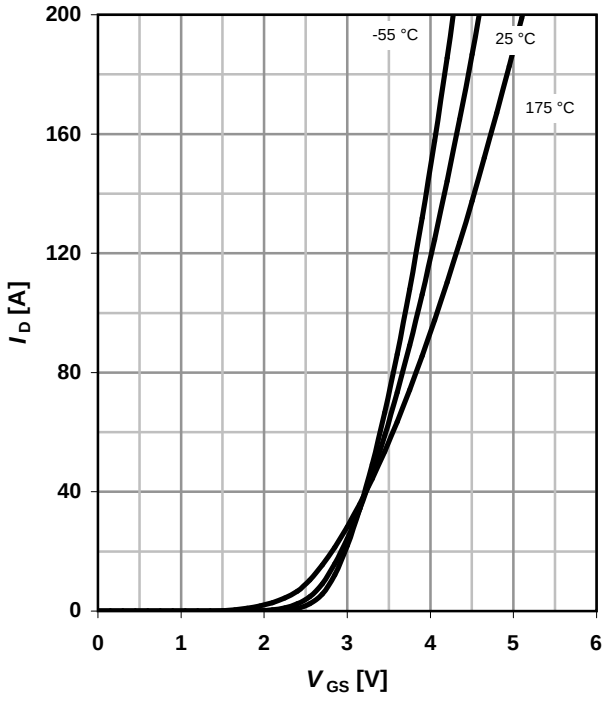
$R_{DS(on)} = f(I_D)$; $T_j = 25$ °C

parameter: V_{GS}

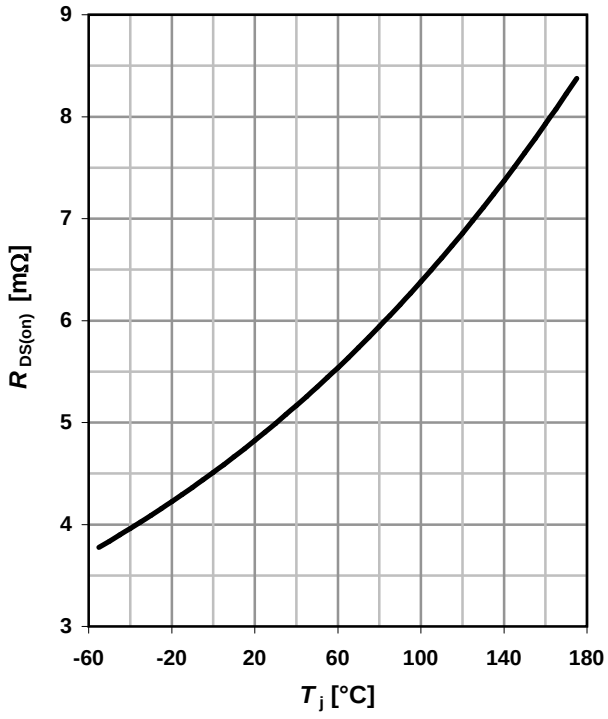


$I_D = f(V_{GS})$; $V_{DS} = 6$V

parameter: T_j



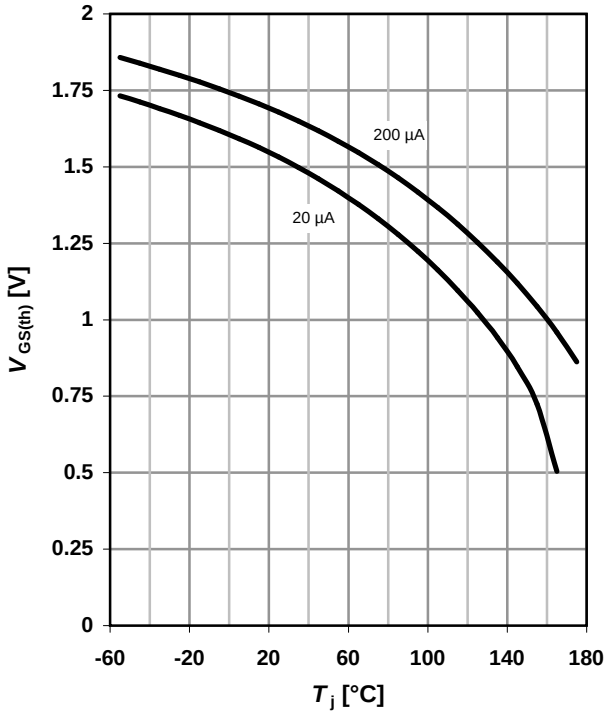
$R_{DS(on)} = f(T_j)$; $I_D = 50$ A; $V_{GS} = 10$ V



9 Typ. gate threshold voltage

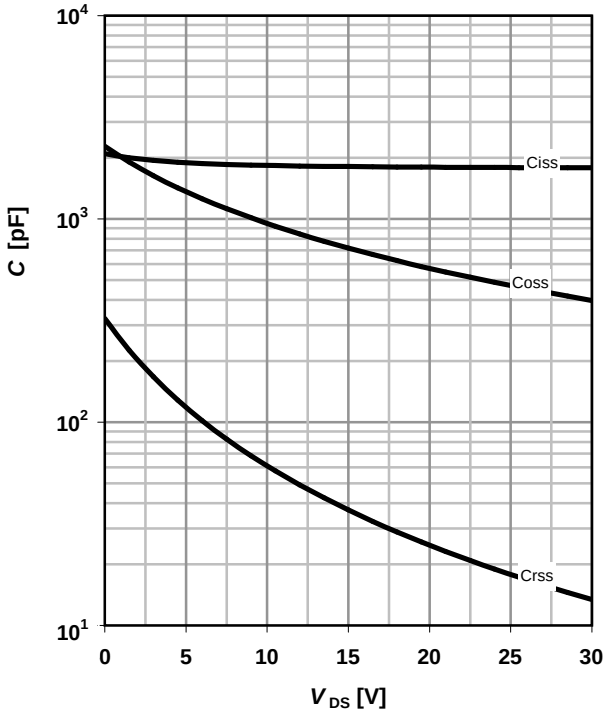
$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$

parameter: I_D



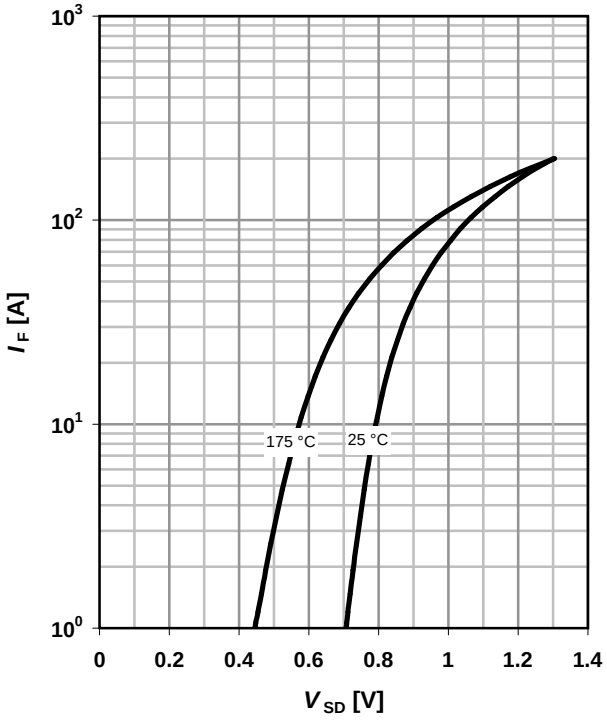
10 Typ. capacitances

$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz



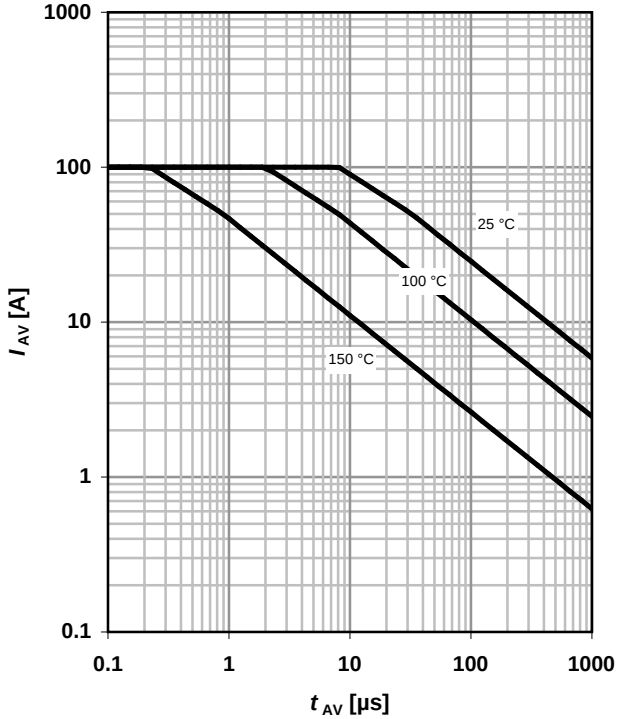
IF = f(V_{SD})

parameter: T_j



$I_{AS} = f(t_{AV})$

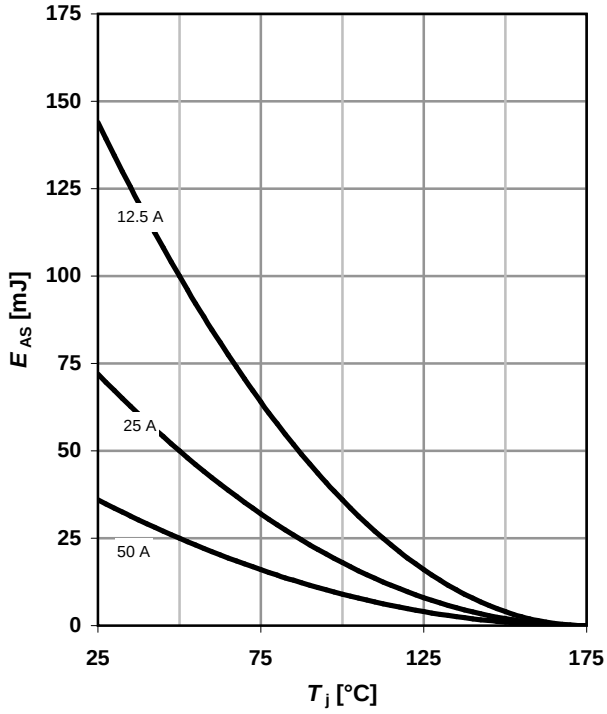
parameter: $T_{j(start)}$



13 Avalanche energy

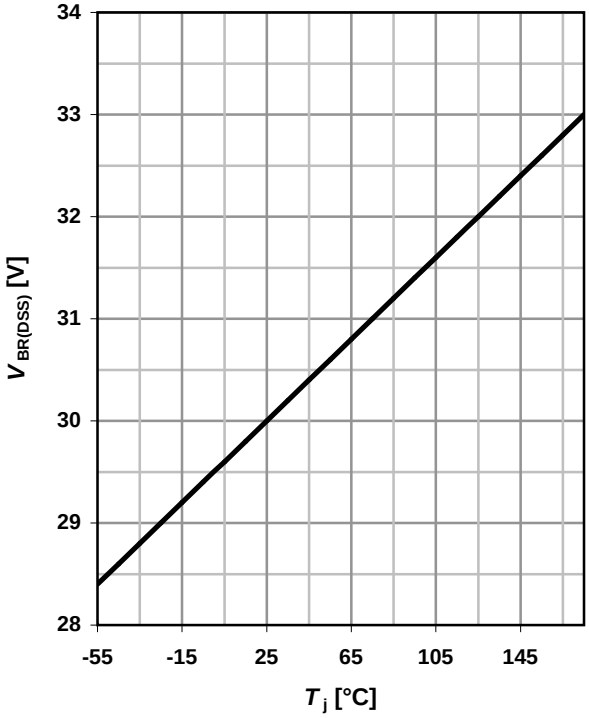
$E_{AS} = f(T_j)$

parameter: I_D



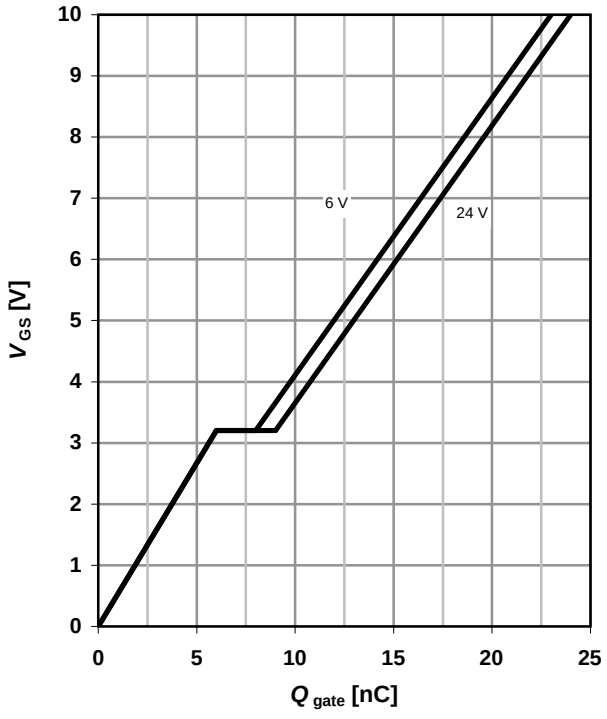
14 Drain-source breakdown voltage

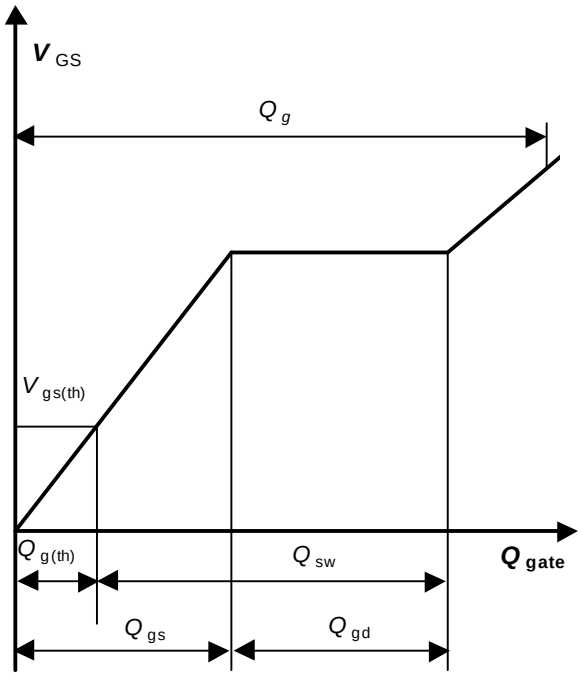
$V_{BR(DSS)} = f(T_j)$; $I_D = 1$ mA



$V_{GS} = f(Q_{gate})$; $I_D = 50$ A pulsed

parameter: V_{DD}





Published by
Infineon Technologies AG
81726 Munich, Germany

Legal Disclaimer
The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information
For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings
Due to technical requirements, components may contain dangerous substances.
For information on the types in question, please contact the nearest Infineon Technologies Office.
Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life.
If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Revision History

Version	Date	Changes
Revision 1.1	05.10.2010	Correction of pinout diagram